

16. (Amended) The transistor of claim 8, wherein the substrate has a bandgap narrower

A2 than a bandgap of silicon.

19. (Amended) A device comprising:

a semiconductor substrate, the substrate being substantially free of silicon;

a well formed in a portion of the substrate, the well having a first type of dopant;

A3
a gate dielectric layer formed over a portion of the well, wherein the gate dielectric
comprises a material having a dielectric constant greater than about 10;

a gate electrode defined over a portion of the gate dielectric layer; and

a source region and a drain region defined proximate the gate electrode in the well, the
source and drain regions being defined by a second type of dopant.--